

Contents

1	Introduction	1
1.1	Ideal Power Switching Waveforms	2
1.2	Ideal and Typical Power MOSFET Characteristics	3
1.3	Typical Power MOSFET Structures	5
1.4	Ideal Drift Region for Unipolar Power Devices	6
1.5	Charge-Coupled Structures: Ideal Specific On-Resistance	8
1.6	Revised Breakdown Models for Silicon	12
1.7	Typical Power MOSFET Applications	18
1.7.1	DC-DC Sync-Buck Converter	18
1.7.2	Variable-Frequency Motor Drive	19
1.8	Summary	21
	References	21
2	D-MOSFET Structure	23
2.1	The D-MOSFET Structure	23
2.2	Power D-MOSFET On-Resistance	25
2.2.1	Channel Resistance	28
2.2.2	Accumulation Resistance	29
2.2.3	JFET Resistance	29
2.2.4	Drift Region Resistance	31
2.2.5	N ⁺ Substrate Resistance	32
2.2.6	Drain and Source Contact Resistance	32
2.2.7	Total On-Resistance	33
2.3	Blocking Voltage	37
2.3.1	Impact of Edge Termination	38
2.3.2	Impact of Graded Doping Profile	39
2.4	Output Characteristics	44
2.4.1	Simulation Example	45
2.5	Device Capacitances	46
2.5.1	Simulation Example	49

2.6	Gate Charge	51
2.6.1	Simulation Example	52
2.7	Device Figures of Merit	54
2.8	Discussion	56
	References	61
3	U-MOSFET Structure	63
3.1	The U-MOSFET Structure	63
3.2	Power U-MOSFET On-Resistance	66
3.2.1	Channel Resistance	67
3.2.2	Accumulation Resistance	68
3.2.3	Drift Region Resistance	68
3.2.4	Total On-Resistance	69
3.3	Blocking Voltage	73
3.3.1	Impact of Edge Termination	74
3.3.2	Impact of Graded Doping Profile	74
3.4	Output Characteristics	80
3.4.1	Simulation Example	80
3.5	Device Capacitances	81
3.5.1	Simulation Example	84
3.6	Gate Charge	86
3.6.1	Simulation Example	88
3.7	Device Figures of Merit	90
3.8	Thick Trench Bottom Oxide Structure	92
3.8.1	On-Resistance	92
3.8.2	Reverse Transfer Capacitance	92
3.8.3	Gate Charge	94
3.8.4	Device Figures-of-Merit	95
3.9	High Voltage Devices	101
3.9.1	Simulation Results	101
3.10	Inductive Load Turn-Off Characteristics	106
3.10.1	Simulation Results	111
3.11	Discussion	112
	References	117
4	SC-MOSFET Structure	119
4.1	The SC-MOSFET Structure	120
4.2	Power SC-MOSFET On-Resistance	122
4.2.1	Channel Resistance	124
4.2.2	Accumulation Resistance	124
4.2.3	JFET Resistance	125
4.2.4	Drift Region Resistance	126
4.2.5	Total On-Resistance	127

4.3	Blocking Voltage	133
4.3.1	Impact of Edge Termination	133
4.4	Output Characteristics	138
4.4.1	Simulation Example	139
4.5	Device Capacitances	139
4.5.1	Simulation Example	144
4.6	Gate Charge	147
4.6.1	Simulation Example	149
4.7	Device Figures of Merit	151
4.8	Discussion	153
	References	158
5	CC-MOSFET Structure	159
5.1	The CC-MOSFET Structure	160
5.2	Charge-Coupling Physics and Blocking Voltage	162
5.2.1	Simulation Results	173
5.3	Power CC-MOSFET On-Resistance	186
5.3.1	Channel Resistance	187
5.3.2	Accumulation Resistance for Current Spreading Region	188
5.3.3	Drift Region Resistance	189
5.3.4	Total On-Resistance	190
5.4	Output Characteristics	195
5.4.1	Simulation Example	195
5.5	Device Capacitances	196
5.5.1	Simulation Example	206
5.6	Gate Charge	209
5.6.1	Simulation Example	214
5.7	Device Figures of Merit	217
5.8	Edge Termination	220
5.8.1	Simulation Example	222
5.9	High Voltage Devices	224
5.9.1	Simulation Results	224
5.10	Process Sensitivity Analysis	232
5.11	Discussion	235
	References	239
6	GD-MOSFET Structure	241
6.1	The GD-MOSFET Structure	242
6.2	Charge-Coupling Physics and Blocking Voltage	244
6.2.1	Simulation Results	250
6.3	Power GD-MOSFET On-Resistance	263
6.3.1	Channel Resistance	265
6.3.2	Accumulation Resistance for Current Spreading Region	266

6.3.3	Drift Region Resistance	266
6.3.4	Total On-Resistance	268
6.4	Output Characteristics	271
6.4.1	Simulation Example	272
6.5	Device Capacitances	273
6.5.1	Simulation Example	276
6.6	Gate Charge	278
6.6.1	Simulation Example	280
6.7	Device Figures of Merit	283
6.8	Edge Termination	285
6.9	High Voltage Devices	285
6.9.1	Simulation Results	286
6.10	Process Sensitivity Analysis	306
6.11	Inductive Load Turn-Off Characteristics	310
6.11.1	Simulation Results	315
6.12	Discussion	317
	References	322
7	SJ-MOSFET Structure	323
7.1	The SJ-MOSFET Structure	324
7.2	Charge-Coupling Physics	326
7.2.1	Simulation Results	329
7.3	Power SJ-MOSFET On-Resistance	346
7.3.1	Channel Resistance	350
7.3.2	Accumulation Resistance for Current Spreading Region	351
7.3.3	Drift Region Resistance	351
7.3.4	Total On-Resistance	353
7.4	Output Characteristics	357
7.4.1	Simulation Example	357
7.5	Device Capacitances	357
7.5.1	Simulation Example	364
7.6	Gate Charge	367
7.6.1	Simulation Example	369
7.7	Device Figures of Merit	371
7.8	Edge Termination	373
7.8.1	Simulation Example	374
7.9	High Voltage Devices	378
7.9.1	Simulation Results	378
7.10	Process Sensitivity Analysis	381
7.11	Inductive Load Turn-Off Characteristics	385
7.11.1	Simulation Results	389
7.12	Discussion	391
	References	396

8	Integral Diode	399
8.1	Power MOSFET Body Diode	400
8.2	Computer Power Supplies	400
8.2.1	Power U–MOSFET Structure	402
8.2.2	Power CC–MOSFET Structure	407
8.2.3	Power JBSFET Structure	412
8.3	Motor Control Application	424
8.3.1	Power U–MOSFET Structure	425
8.3.2	Power JBSFET Structure	430
8.3.3	Power GD–MOSFET Structure	437
8.3.4	Power GD–JBSFET Structure	443
8.3.5	Power SJ–MOSFET Structure	461
8.3.6	Power SJ–JBSFET Structure	467
8.4	Discussion	472
8.4.1	Low–Voltage Devices	473
8.4.2	High–Voltage Devices	474
	References	476
9	SiC Planar MOSFET Structures	477
9.1	Shielded Planar Inversion-Mode MOSFET Structure	478
9.1.1	Blocking Mode	479
9.1.2	Threshold Voltage	484
9.1.3	On–State Resistance	486
9.1.4	Capacitances	493
9.1.5	Gate Charge	496
9.1.6	Device Figures of Merit	498
9.1.7	Inductive Load Turn-Off Characteristics	499
9.1.8	Body-Diode Characteristics	503
9.2	Shielded Planar ACCUFET Structure	504
9.2.1	Blocking Mode	505
9.2.2	Threshold Voltage	510
9.2.3	On–State Resistance	512
9.2.4	Capacitances	517
9.2.5	Gate Charge	519
9.2.6	Device Figures of Merit	522
9.2.7	Inductive Load Turn-Off Characteristics	523
9.2.8	Body–Diode Characteristics	527
9.3	Discussion	531
	References	533
10	Synopsis	535
10.1	Computer Power Supplies	536
10.1.1	Inadvertent Turn–On Suppression	537
10.1.2	Device Active Area	539

10.1.3 Switching Power Losses	540
10.1.4 Input Capacitance	540
10.1.5 Device Comparison	540
10.2 High Voltage Motor Control	543
10.3 Device Comparison	549
10.4 Summary	552
References	552
About the Author	553
Index	557



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